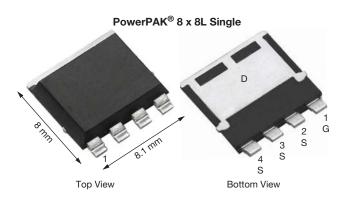


Vishay Siliconix

## Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0012
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0015
I <sub>D</sub> (A)	200
Configuration	Single
Package	PowerPAK 8 x 8L

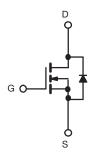
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



N-Channel MOSFET

PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V <sub>DS</sub>	40			
Gate-source voltage	V <sub>GS</sub>	± 20	V		
Continuous drain current	T <sub>C</sub> = 25 °C <sup>a</sup>	1	200	A	
	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	141		
Continuous source current (diode conduct	ion)	I <sub>S</sub>	136		
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	600			
Single pulse avalanche current	. 0.1!!	I <sub>AS</sub>	50		
Single pulse avalanche energy	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
Maximum power dissipation	T <sub>C</sub> = 25 °C	D	150	10/	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	50	W	
Operating junction and storage temperature	re range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature)	<u> </u>	260	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W
Junction-to-case (drain)		$R_{thJC}$	1	G/VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

## Vishay Siliconix

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		40	-	-	V	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2	2.5	\ \	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	500		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	100	-	-	Α	
Drain-source on-state resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0009	0.0012	Ω	
	D	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10 A	-	0.0011	0.0015		
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0018		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0022		
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		-	122	-	S	
Dynamic <sup>b</sup>								
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 25 V, f = 1 MHz	-	10 810	14 500	pF	
Output capacitance	C <sub>oss</sub>			-	6500	8500		
Reverse transfer capacitance	C <sub>rss</sub>	]		-	700	950		
Total gate charge <sup>c</sup>	Qg		V <sub>DS</sub> = 20 V, I <sub>D</sub> = 10 A	-	140	220	nC	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V		-	30	-		
Gate-drain charge <sup>c</sup>	$Q_{gd}$			-	20	-		
Gate resistance	$R_g$	f = 1 MHz		0.45	0.99	1.50	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	24	40		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 20 \text{ V, } R_L = 2 \Omega$ $I_D \cong 10 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	60	100	ns	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	60	100		
Fall time <sup>c</sup>	t <sub>f</sub>			-	30	50		
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α	
Forward voltage	$V_{SD}$	· .	= 50 A, V <sub>GS</sub> = 0		0.8	1.2	V	

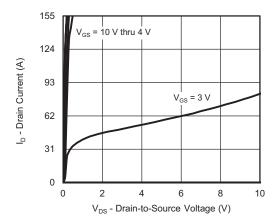
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

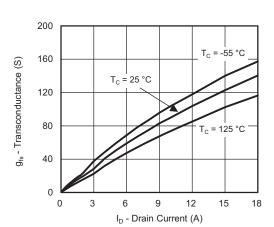
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



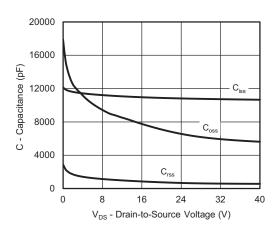
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



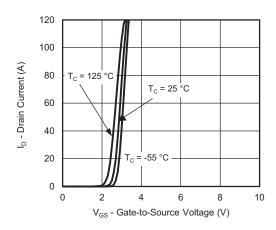
#### **Output Characteristics**



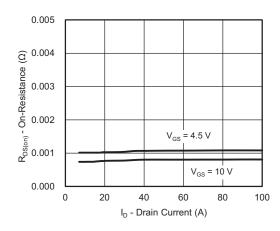
Transconductance



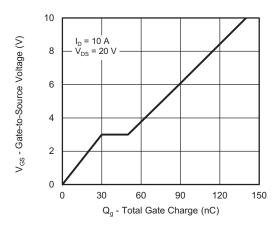
Capacitance



**Transfer Characteristics** 



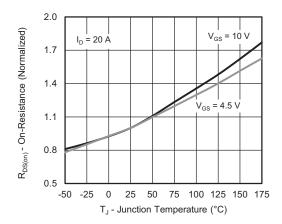
**On-Resistance vs. Drain Current** 



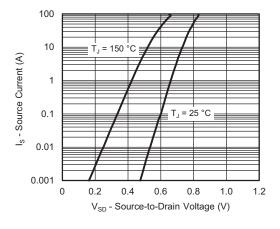
**Gate Charge** 



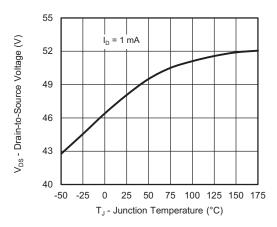
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



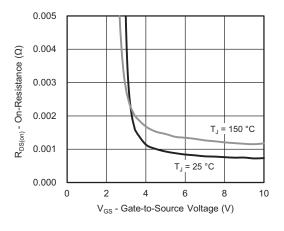
On-Resistance vs. Junction Temperature



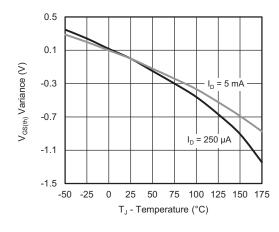
**Source Drain Diode Forward Voltage** 



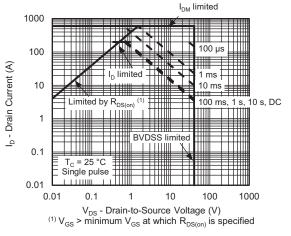
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

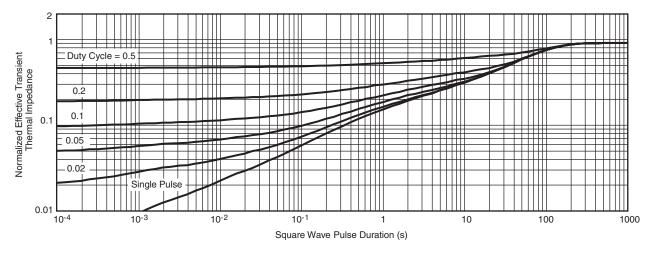


Safe Operating Area

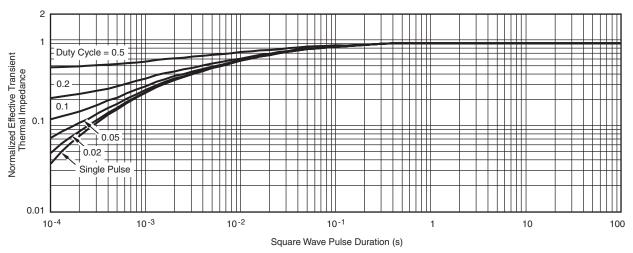
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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?68443">www.vishay.com/ppg?68443</a>.

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## PowerPAK® 8 x 8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK 8 x 8L package:

DATASHEET PART NUMBER	OLD ORDERING CODE <sup>a</sup>	NEW ORDERING CODE
SQJQ100EL	-	SQJQ100EL-T1_GE3
SQJQ402E	SQJQ402E-T1-GE3	SQJQ402E-T1_GE3
SQJQ410EL	-	SQJQ410EL-T1_GE3
SQJQ900E	-	SQJQ900E-T1_GE3

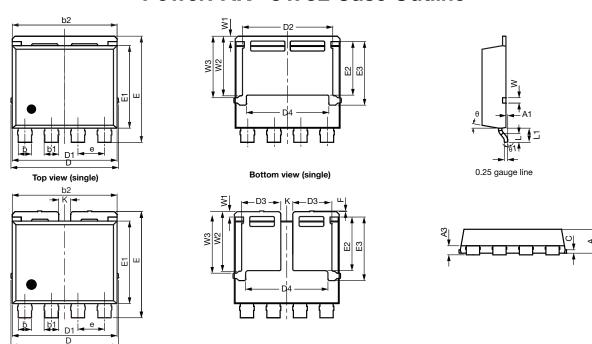
#### Note

a. Old ordering code is obsolete and no longer valid for new orders



Top view (dual)

## PowerPAK® 8 x 8L Case Outline



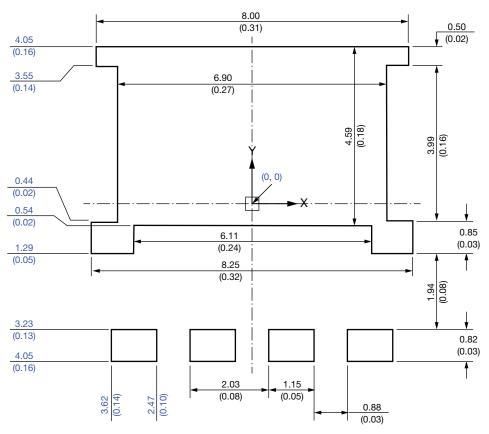
Bottom view (dual)

DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	1.70	1.80	1.90	0.067	0.071	0.075		
A1	0.00	0.08	0.13	0.000	0.003	0.005		
A3	0.55	0.62	0.70	0.022	0.024	0.028		
b	0.92	1.00	1.08	0.036	0.039	0.043		
b1	1.02	1.10	1.18	0.040	0.043	0.046		
b2	7.80	7.90	8.00	0.307	0.311	0.315		
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	8.00	8.10	8.25	0.315	0.319	0.325		
D1	7.80	7.90	8.00	0.307	0.311	0.315		
D2	6.70	6.80	6.90	0.264	0.268	0.272		
D3	2.85	2.95	3.05	0.112	0.116	0.120		
D4	6.11	6.21	6.31	0.241	0.244	0.248		
е	1.95	2.00	2.05	0.077	0.079	0.081		
E	7.90	8.00	8.10	0.311	0.315	0.319		
E1	6.12	6.22	6.32	0.241	0.245	0.249		
E2	3.94	4.04	4.14	0.140	0.159	0.163		
E3	4.69	4.79	4.89	0.185	0.189	0.193		
F	0.05	0.10	0.15	0.002	0.004	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K	0.80	0.90	1.00	0.031	0.035	0.039		
W	0.30	0.40	0.50	0.012	0.016	0.020		
W1	0.30	0.40	0.50	0.012	0.016	0.020		
W2	4.39	4.49	4.59	0.173	0.177	0.181		
W3	4.54	4.64	4.74	0.179	0.183	0.187		
θ	6°	10°	14°	6°	10°	14°		
θ1	0°	3°	8°	0°	3°	8°		
θ1 -0891-Rev. A, G: 6026	ŭ	3°	8°	0°	3°			

Revision: 06-Oct-14 1 Document Number: 67734



# Recommended Minimum PADs for PowerPAK® 8 x 8L Single



#### Dimensions in millimeters (inches)

#### Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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Revision: 13-Jun-16 1 Document Number: 91000